

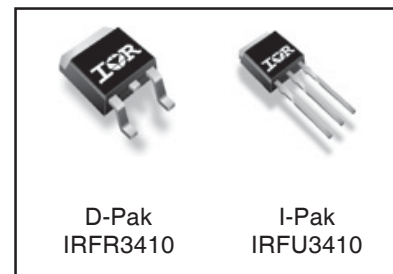
### Applications

- High frequency DC-DC converters

| $V_{DS}$ | $R_{DS(on)}$ max | $I_D$            |
|----------|------------------|------------------|
| 100V     | 39m $\Omega$     | 31A <sup>⑥</sup> |

### Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



### Absolute Maximum Ratings

| Symbol                                  | Parameter                                       | Max.                   | Units |
|-----------------------------------------|-------------------------------------------------|------------------------|-------|
| V <sub>DS</sub>                         | Drain-Source Voltage                            | 100                    | V     |
| V <sub>GS</sub>                         | Gate-to-Source Voltage                          | ± 20                   |       |
| I <sub>D</sub> @ T <sub>C</sub> = 25°C  | Continuous Drain Current, V <sub>GS</sub> @ 10V | 31⑥                    | A     |
| I <sub>D</sub> @ T <sub>C</sub> = 100°C | Continuous Drain Current, V <sub>GS</sub> @ 10V | 22                     |       |
| I <sub>DM</sub>                         | Pulsed Drain Current①                           | 125                    |       |
| P <sub>D</sub> @T <sub>C</sub> = 25°C   | Maximum Power Dissipation                       | 110                    | W     |
| P <sub>D</sub> @T <sub>A</sub> = 25°C   | Maximum Power Dissipation                       | 3.0                    |       |
|                                         | Linear Derating Factor                          | 0.71                   | W°C   |
| dv/dt                                   | Peak Diode Recovery dv/dt ③                     | 15                     | V/ns  |
| T <sub>J</sub>                          | Operating Junction and                          | -55 to + 175           | °C    |
| T <sub>STG</sub>                        | Storage Temperature Range                       |                        |       |
|                                         | Soldering Temperature, for 10 seconds           | 300 (1.6mm from case ) |       |

### Thermal Resistance

|                 | Parameter                        | Typ. | Max. | Units                     |
|-----------------|----------------------------------|------|------|---------------------------|
| $R_{\theta JC}$ | Junction-to-Case                 | —    | 1.4  | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB mount)* | —    | 40   |                           |
| $R_{\theta JA}$ | Junction-to-Ambient              | —    | 110  |                           |

Notes ① through ⑥ are on page 10

www.irf.com

**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

|                                 | Parameter                            | Min. | Typ. | Max. | Units               | Conditions                                                 |
|---------------------------------|--------------------------------------|------|------|------|---------------------|------------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 100  | —    | —    | V                   | $V_{GS} = 0V$ , $I_D = 250\mu A$                           |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.11 | —    | V/ $^\circ\text{C}$ | Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$ ④     |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | 34   | 39   | m $\Omega$          | $V_{GS} = 10V$ , $I_D = 18A$ ④                             |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.0  | —    | 4.0  | V                   | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$                       |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —    | 20   | $\mu A$             | $V_{DS} = 100V$ , $V_{GS} = 0V$                            |
|                                 |                                      | —    | —    | 250  |                     | $V_{DS} = 80V$ , $V_{GS} = 0V$ , $T_J = 150^\circ\text{C}$ |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 200  | nA                  | $V_{GS} = 20V$                                             |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -200 |                     | $V_{GS} = -20V$                                            |

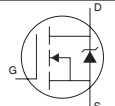
**Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

|                        | Parameter                       | Min. | Typ. | Max. | Units | Conditions                                                             |
|------------------------|---------------------------------|------|------|------|-------|------------------------------------------------------------------------|
| $g_{fs}$               | Forward Transconductance        | 33   | —    | —    | S     | $V_{DS} = 25V$ , $I_D = 18A$                                           |
| $Q_g$                  | Total Gate Charge               | —    | 37   | 56   | nC    | $I_D = 18A$<br>$V_{DS} = 50V$<br>$V_{GS} = 10V$ , ④                    |
| $Q_{gs}$               | Gate-to-Source Charge           | —    | 10   | —    |       |                                                                        |
| $Q_{gd}$               | Gate-to-Drain ("Miller") Charge | —    | 11   | —    |       |                                                                        |
| $t_{d(on)}$            | Turn-On Delay Time              | —    | 12   | —    | ns    | $V_{DD} = 50V$<br>$I_D = 18A$<br>$R_G = 9.1\Omega$<br>$V_{GS} = 10V$ ④ |
| $t_r$                  | Rise Time                       | —    | 27   | —    |       |                                                                        |
| $t_{d(off)}$           | Turn-Off Delay Time             | —    | 40   | —    |       |                                                                        |
| $t_f$                  | Fall Time                       | —    | 13   | —    |       |                                                                        |
| $C_{iss}$              | Input Capacitance               | —    | 1690 | —    | pF    | $V_{GS} = 0V$                                                          |
| $C_{oss}$              | Output Capacitance              | —    | 220  | —    |       | $V_{DS} = 25V$                                                         |
| $C_{rss}$              | Reverse Transfer Capacitance    | —    | 26   | —    |       | $f = 1.0\text{MHz}$                                                    |
| $C_{oss}$              | Output Capacitance              | —    | 1640 | —    |       | $V_{GS} = 0V$ , $V_{DS} = 1.0V$ , $f = 1.0\text{MHz}$                  |
| $C_{oss}$              | Output Capacitance              | —    | 130  | —    |       | $V_{GS} = 0V$ , $V_{DS} = 80V$ , $f = 1.0\text{MHz}$                   |
| $C_{oss \text{ eff.}}$ | Effective Output Capacitance    | —    | 250  | —    |       | $V_{GS} = 0V$ , $V_{DS} = 0V$ to $80V$ ⑤                               |

**Avalanche Characteristics**

|          | Parameter                      | Typ. | Max. | Units |
|----------|--------------------------------|------|------|-------|
| $E_{AS}$ | Single Pulse Avalanche Energy② | —    | 140  | mJ    |
| $I_{AR}$ | Avalanche Current①             | —    | 18   | A     |

**Diode Characteristics**

|          | Parameter                              | Min.                                                                        | Typ. | Max. | Units | Conditions                                                                                                                                           |
|----------|----------------------------------------|-----------------------------------------------------------------------------|------|------|-------|------------------------------------------------------------------------------------------------------------------------------------------------------|
| $I_S$    | Continuous Source Current (Body Diode) | —                                                                           | —    | 31⑥  | A     | MOSFET symbol showing the integral reverse p-n junction diode.  |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ①   | —                                                                           | —    | 125  |       |                                                                                                                                                      |
| $V_{SD}$ | Diode Forward Voltage                  | —                                                                           | —    | 1.3  | V     | $T_J = 25^\circ\text{C}$ , $I_S = 18A$ , $V_{GS} = 0V$ ④                                                                                             |
| $t_{rr}$ | Reverse Recovery Time                  | —                                                                           | 84   | —    | ns    | $T_J = 25^\circ\text{C}$ , $I_F = 18A$                                                                                                               |
| $Q_{rr}$ | Reverse Recovery Charge                | —                                                                           | 260  | —    | nC    | $di/dt = 100A/\mu s$ ④                                                                                                                               |
| $t_{on}$ | Forward Turn-On Time                   | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ ) |      |      |       |                                                                                                                                                      |

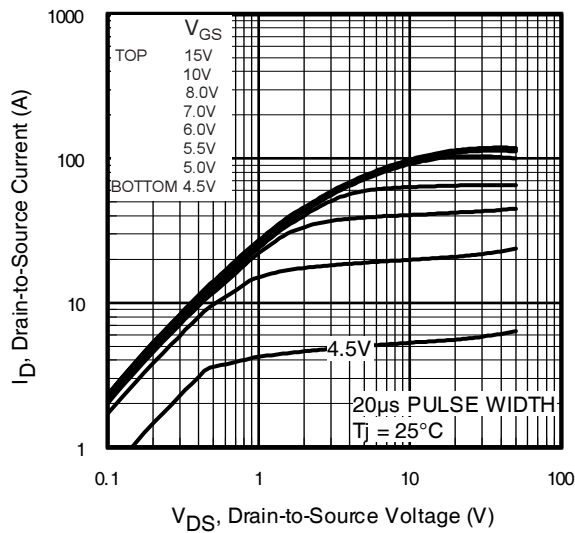


Fig 1. Typical Output Characteristics

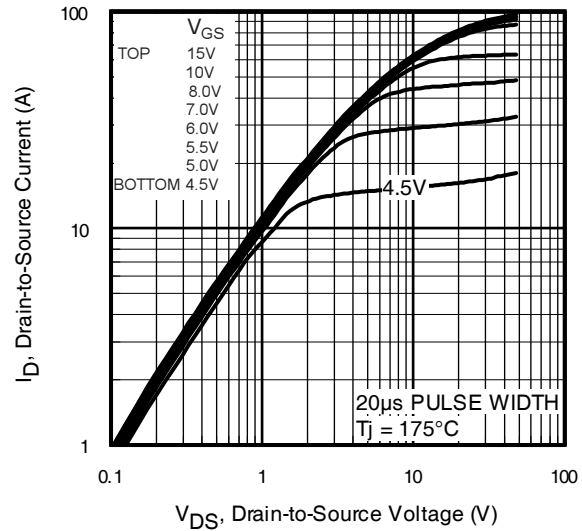


Fig 2. Typical Output Characteristics

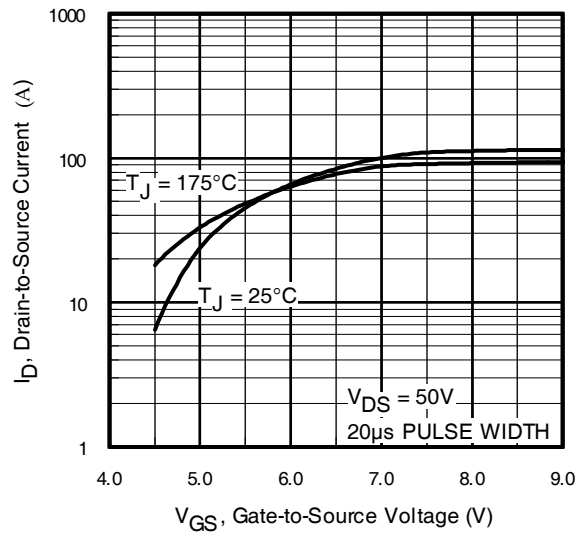


Fig 3. Typical Transfer Characteristics

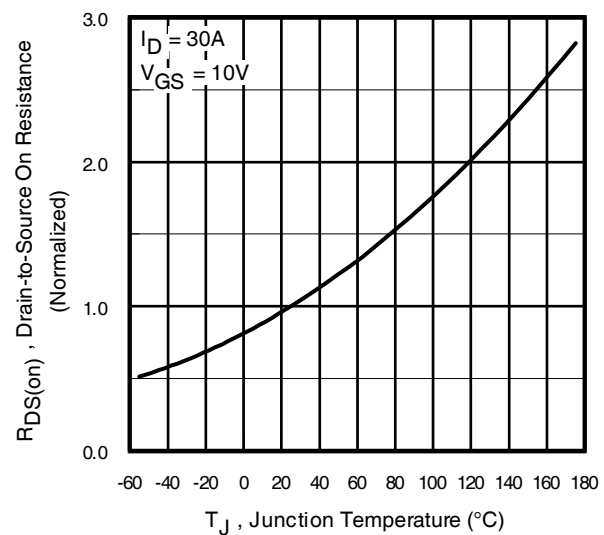
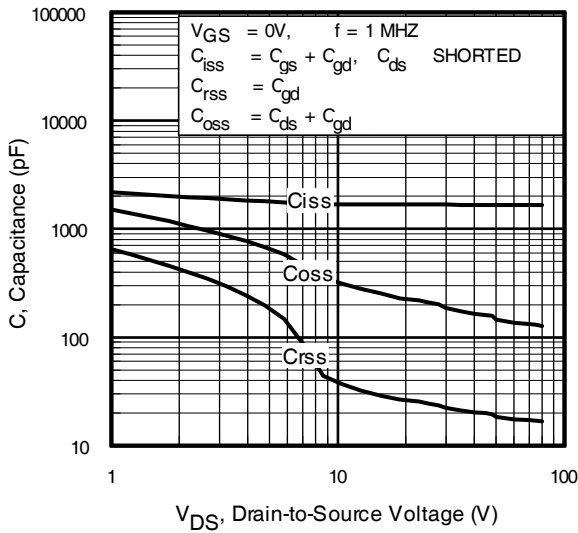
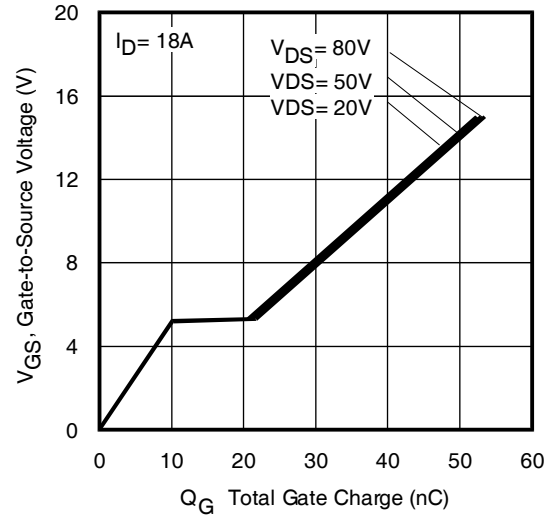


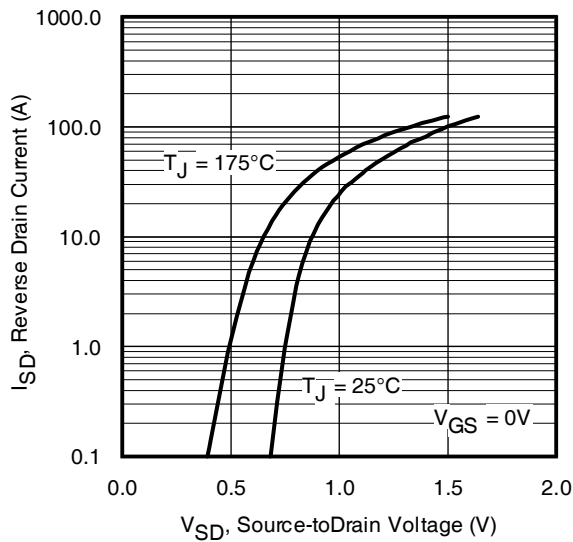
Fig 4. Normalized On-Resistance Vs. Temperature



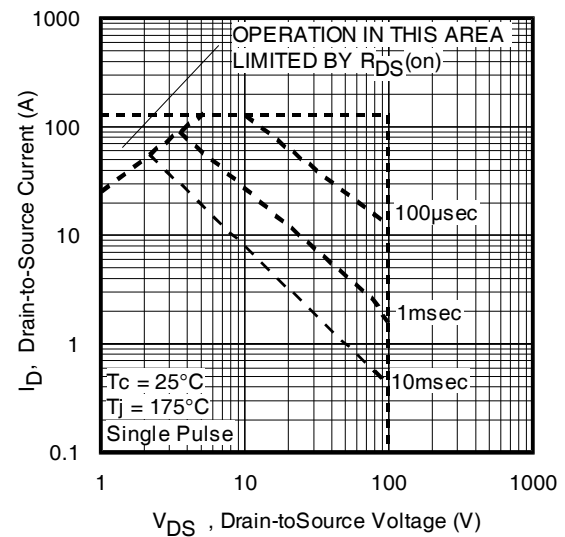
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



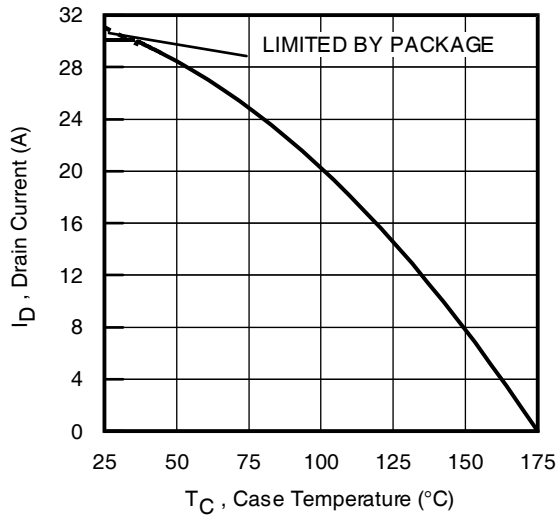
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



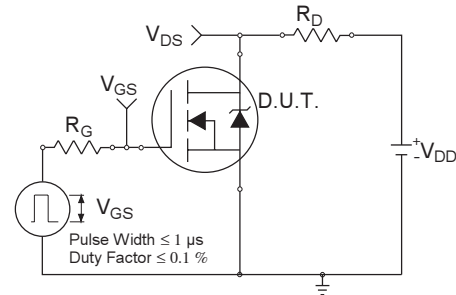
**Fig 7.** Typical Source-Drain Diode Forward Voltage



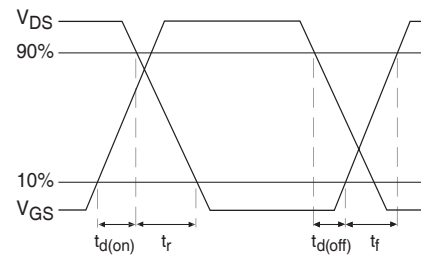
**Fig 8.** Maximum Safe Operating Area



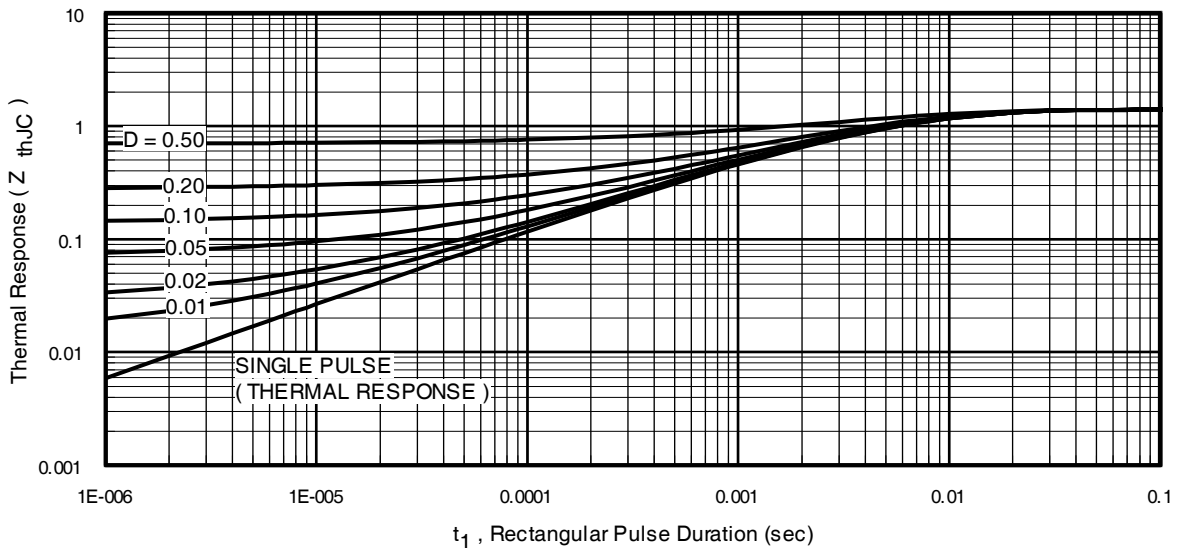
**Fig 9.** Maximum Drain Current Vs. Case Temperature



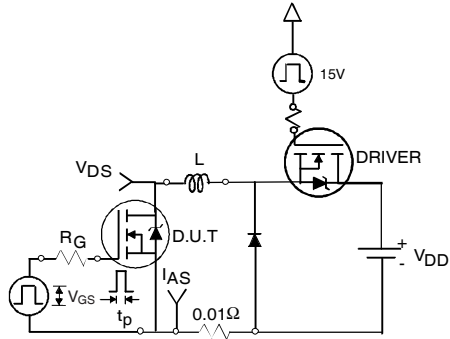
**Fig 10a.** Switching Time Test Circuit



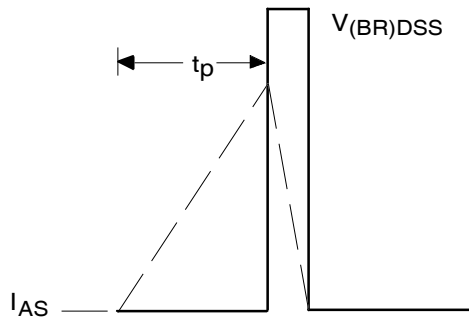
**Fig 10b.** Switching Time Waveforms



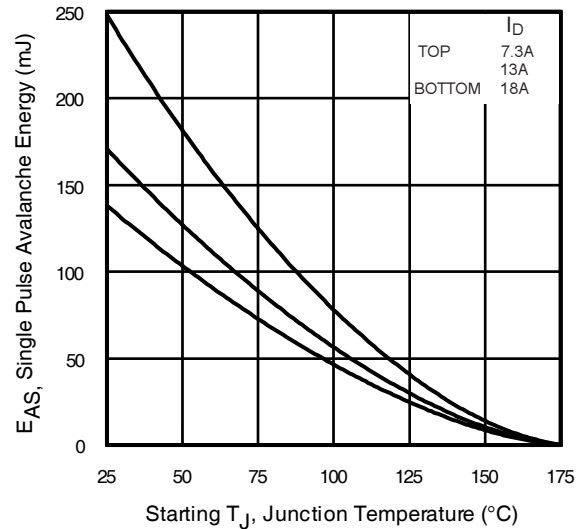
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



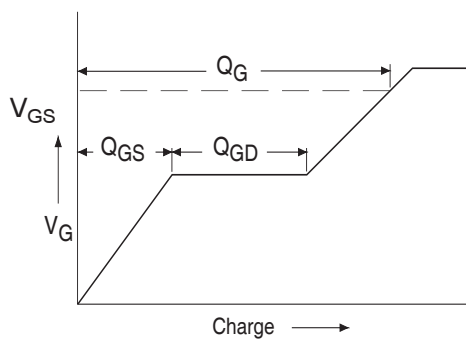
**Fig 12a.** Unclamped Inductive Test Circuit



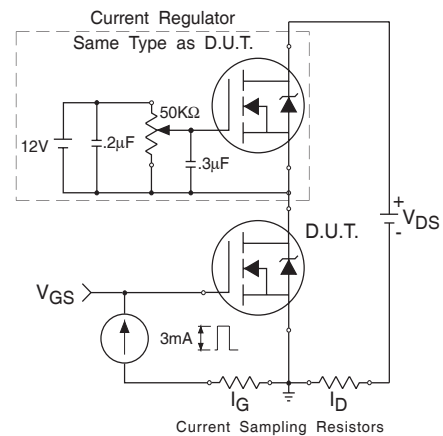
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

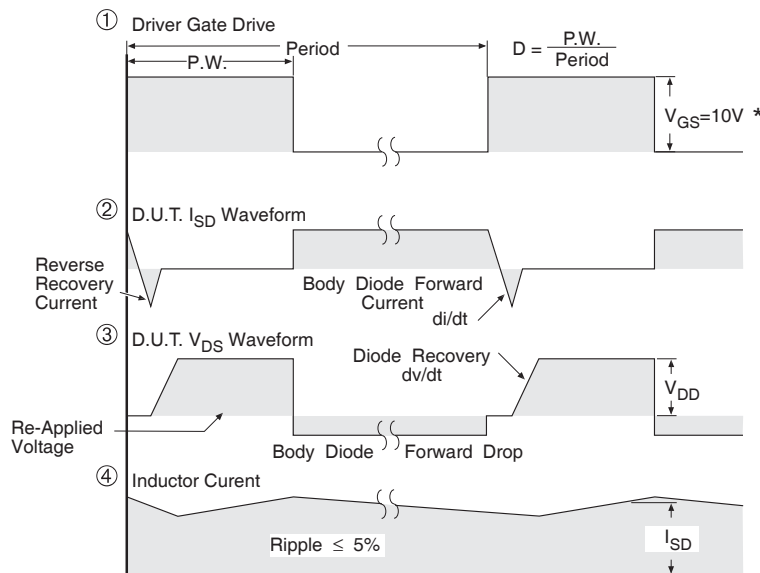
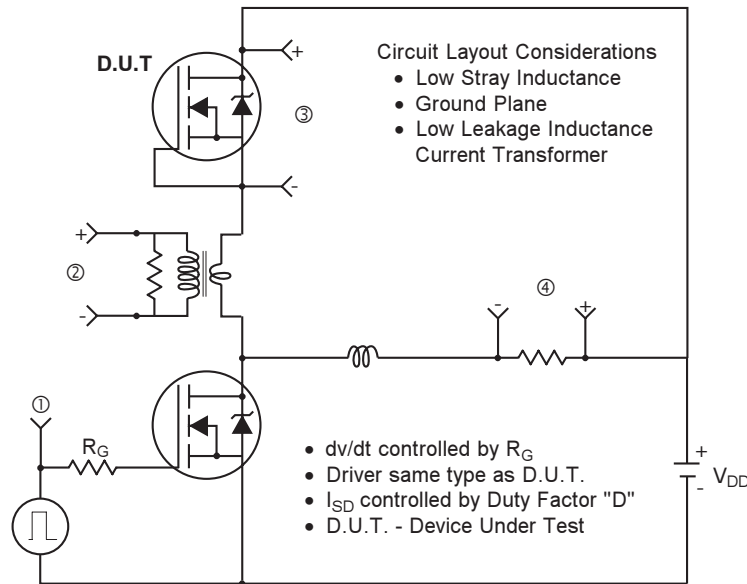


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

### Peak Diode Recovery $dv/dt$ Test Circuit



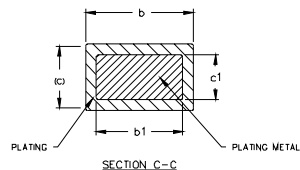
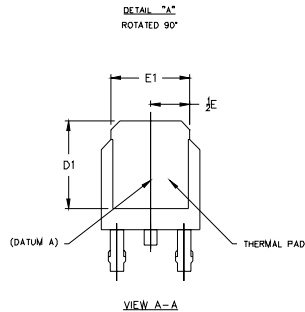
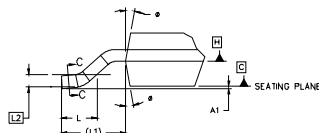
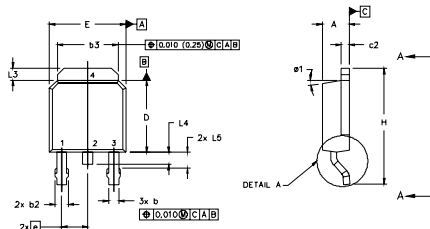
\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRFR/U3410

International  
**IR** Rectifier

## D-Pak (TO-252AA) Package Outline



### NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.0 LEAD DIMENSION UNCONTROLLED IN L5
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.254] FROM THE LEAD TIP.
- 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

| SYMBOL | DIMENSIONS  |        |           |      | NOTES |
|--------|-------------|--------|-----------|------|-------|
|        | MILLIMETERS |        | INCHES    |      |       |
|        | MIN.        | MAX.   | MIN.      | MAX. |       |
| A      | 2.18        | 2.39   | .088      | .094 |       |
| A1     |             | 0.13   |           | .005 |       |
| b      | 0.64        | 0.89   | .025      | .035 | 5     |
| b1     | 0.64        | 0.79   | .025      | .031 | 5     |
| b2     | 0.76        | 1.14   | .030      | .045 |       |
| b3     | 4.95        | 5.46   | .195      | .215 |       |
| c      | 0.46        | 0.61   | .018      | .024 | 5     |
| c1     | 0.41        | 0.56   | .016      | .022 | 5     |
| c2     | .046        | 0.89   | .018      | .035 | 5     |
| D      | 5.97        | 6.22   | .235      | .245 | 6     |
| D1     | 5.21        | -      | .205      | -    | 4     |
| E      | 6.35        | 6.73   | .250      | .265 | 6     |
| E1     | 4.32        | -      | .170      | -    | 4     |
| e      | 2.29        |        | .090 BSC  |      |       |
| H      | 9.40        | 10.41  | .370      | .410 |       |
| L      | 1.40        | 1.78   | .055      | .070 |       |
| L1     | 2.74 REF.   |        | .108 REF. |      |       |
| L2     | 0.651 BSC   |        | .020 BSC  |      |       |
| L3     | 0.89        | 1.27   | .035      | .050 |       |
| L4     |             | 1.02   |           | .040 |       |
| L5     | 1.14        | 1.52   | .045      | .060 | 3     |
| #      | 0" 10"      | 0" 10" |           |      |       |
| #1     | 0" 15"      | 0" 15" |           |      |       |

### LEAD ASSIGNMENTS

#### HEXFET

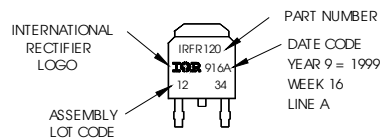
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

#### IGBTs, CoPACK

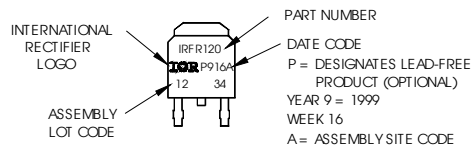
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

## D-Pak (TO-252AA) Part Marking Information

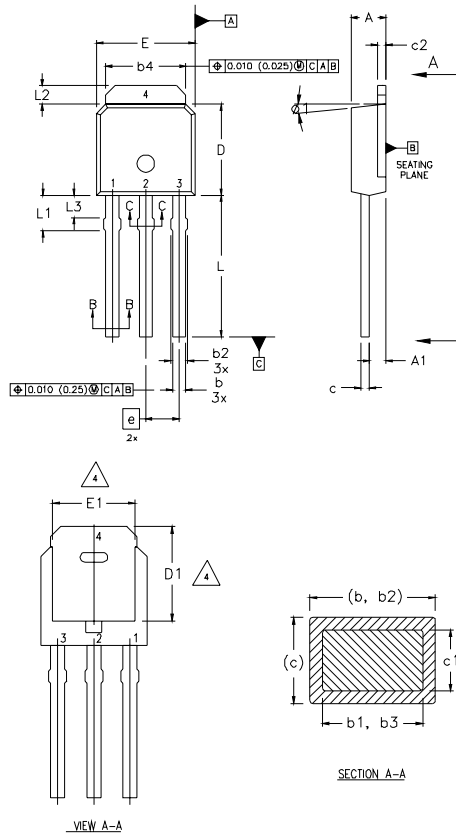
EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"  
Note: "P" in assembly line  
position indicates "Lead-Free"



OR



## I-Pak (TO-251AA) Package Outline



### NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

### LEAD ASSIGNMENTS

#### HEXFET

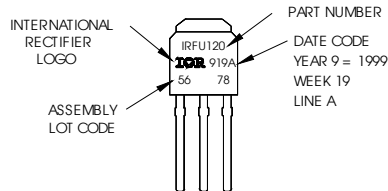
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

| SYMBOL | DIMENSIONS  |      |           |       | NOTES |
|--------|-------------|------|-----------|-------|-------|
|        | MILLIMETERS |      | INCHES    |       |       |
|        | MIN.        | MAX. | MIN.      | MAX.  |       |
| A      | 2.18        | 2.39 | 0.086     | .094  |       |
| A1     | 0.89        | 1.14 | 0.035     | 0.045 |       |
| b      | 0.64        | 0.89 | 0.025     | 0.035 |       |
| b1     | 0.64        | 0.79 | 0.025     | 0.031 | 4     |
| b2     | 0.76        | 1.14 | 0.030     | 0.045 |       |
| b3     | 0.76        | 1.04 | 0.030     | 0.041 |       |
| b4     | 5.00        | 5.46 | 0.195     | 0.215 | 4     |
| c      | 0.46        | 0.61 | 0.018     | 0.024 |       |
| c1     | 0.41        | 0.56 | 0.016     | 0.022 |       |
| c2     | .046        | 0.86 | 0.018     | 0.035 |       |
| D      | 5.97        | 6.22 | 0.235     | 0.245 | 3, 4  |
| D1     | 5.21        | —    | 0.205     | —     | 4     |
| E      | 6.35        | 6.73 | 0.250     | 0.265 | 3, 4  |
| E1     | 4.32        | —    | 0.170     | —     | 4     |
| e      | 2.29        |      | 0.090 BSC |       |       |
| L      | 8.89        | 9.60 | 0.350     | 0.380 |       |
| L1     | 1.91        | 2.29 | 0.075     | 0.090 |       |
| L2     | 0.89        | 1.27 | 0.035     | 0.050 | 4     |
| L3     | 1.14        | 1.52 | 0.045     | 0.060 | 5     |
| ø1     | 0"          | 15'  | 0"        | 15'   |       |

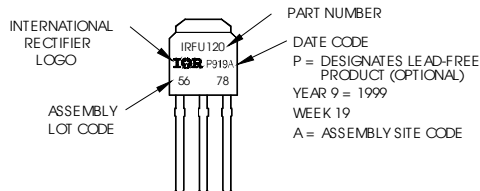
## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120  
WITH ASSEMBLY  
LOT CODE 5678  
ASSEMBLED ON WW 19, 1999  
IN THE ASSEMBLY LINE "A"

**Note:** "P" in assembly line position indicates "Lead-Free"



OR

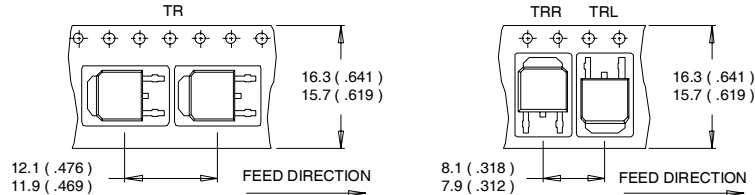


# IRFR/U3410

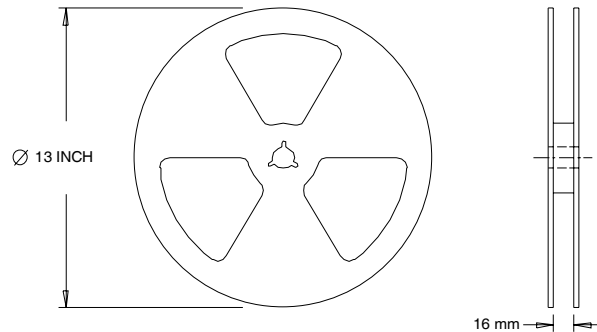
International  
**IR** Rectifier

## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
  - ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.85\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 18\text{A}$ .
  - ③  $I_{SD} \leq 18\text{A}$ ,  $di/dt \leq 360\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$
  - ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
  - ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
  - ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- \* When mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.2/06

[www.irf.com](http://www.irf.com)

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>